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[ON Semiconductor](#)

[MBRD835LT4](#)

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MBRD835L

Preferred Device

SWITCHMODE™ Power Rectifier

DPAK Surface Mount Package

This SWITCHMODE power rectifier which uses the Schottky Barrier principle with a proprietary barrier metal, is designed for use as output rectifiers, free wheeling, protection and steering diodes in switching power supplies, inverters and other inductive switching circuits.

Features

- Low Forward Voltage
- 150°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Compact Size
- Lead Formed for Surface Mount
- Pb-Free Packages are Available

Mechanical Characteristics

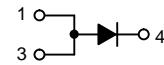
- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 75 Units Per Plastic Tube
- Available in 16 mm Tape and Reel, 2500 Units Per 13 in Reel, by Adding a "T4" Suffix to the Part Number
- ESD Rating: Machine Model = C (> 400 V)
Human Body Model = 3B (> 8000 V)



ON Semiconductor®

<http://onsemi.com>

SCHOTTKY BARRIER RECTIFIER 8.0 AMPERES, 35 VOLTS



MARKING DIAGRAM



Y = Year
 WW = Work Week
 G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping†
MBRD835L	DPAK	75 Units/Rail
MBRD835LG	DPAK (Pb-Free)	75 Units/Rail
MBRD835LT4	DPAK	2500/Tape & Reel
MBRD835LT4G	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	V
Average Rectified Forward Current (At Rated V_R , $T_C = 88^\circ\text{C}$)	$I_{F(AV)}$	8.0	A
Peak Repetitive Forward Current (At Rated V_R , Square Wave, 20 kHz, $T_C = 80^\circ\text{C}$)	I_{FRM}	16	A
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	75	A
Repetitive Avalanche Current (Current Decaying Linearly to Zero in 1 μs , Frequency Limited by T_{Jmax})	I_{AR}	2.0	A
Storage / Operating Case Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature (Note 1)	T_J	-65 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	$\text{V}/\mu\text{s}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance – Junction-to-Case	$R_{\theta JC}$	2.8	$^\circ\text{C}/\text{W}$
Thermal Resistance – Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 3) (if = 8 Amps, $T_C = +25^\circ\text{C}$) (if = 8 Amps, $T_C = +125^\circ\text{C}$)	V_F	0.51 0.41	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, $T_C = +25^\circ\text{C}$) (Rated dc Voltage, $T_C = +100^\circ\text{C}$)	I_R	1.4 35	mA

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.
2. Rating applies when surface mounted on the minimum pad size recommended.
3. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

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TYPICAL CHARACTERISTICS

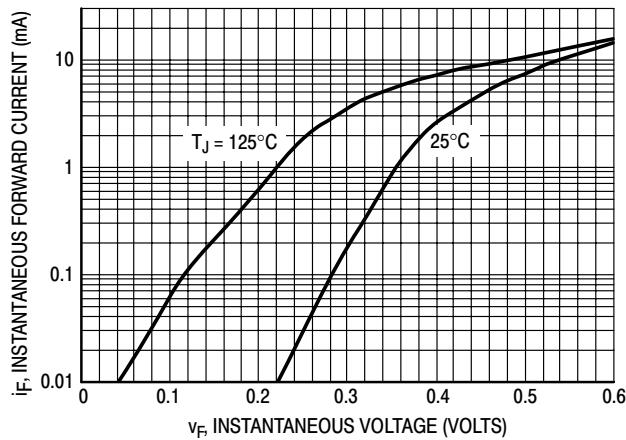


Figure 1. Maximum Forward Voltage

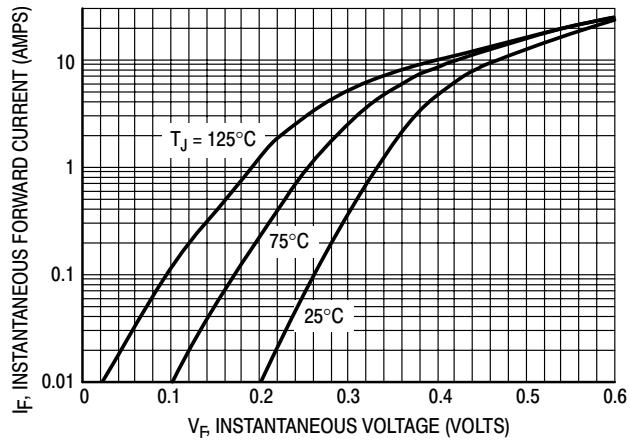


Figure 2. Typical Forward Voltage

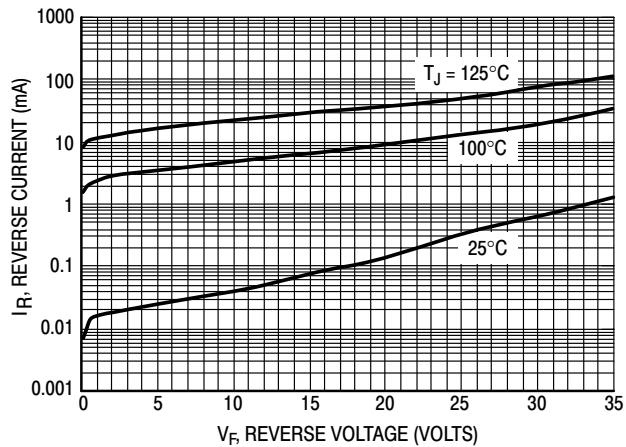


Figure 3. Maximum Reverse Current

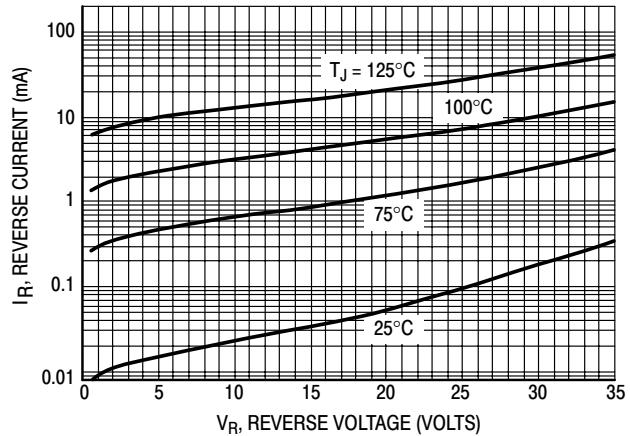


Figure 4. Typical Reverse Current

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TYPICAL CHARACTERISTICS

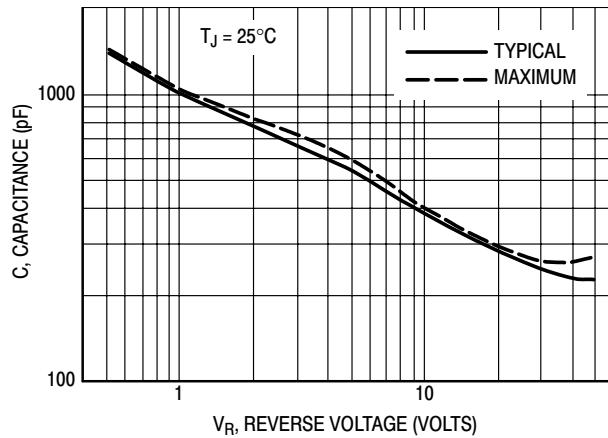


Figure 5. Maximum and Typical Capacitance

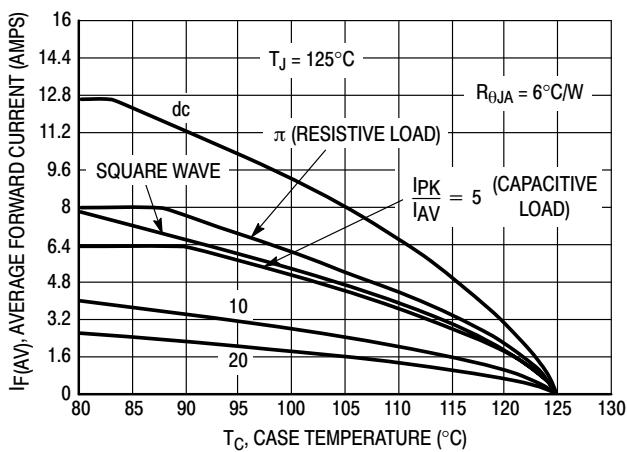


Figure 6. Current Derating, Infinite Heatsink

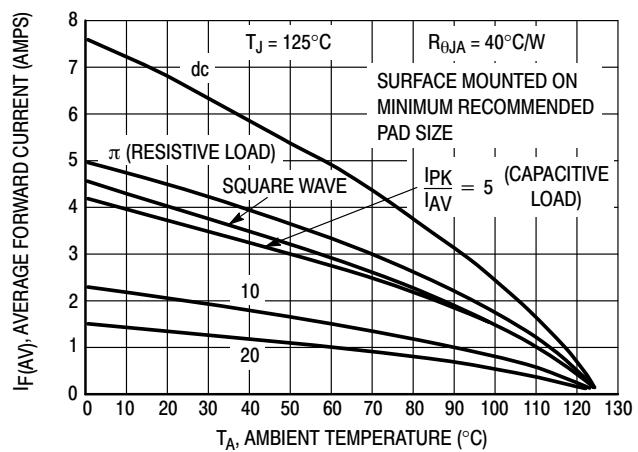


Figure 7. Current Derating

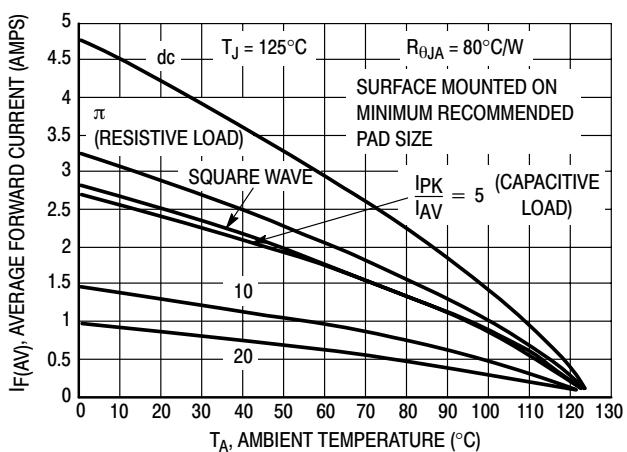


Figure 8. Current Derating, Free Air

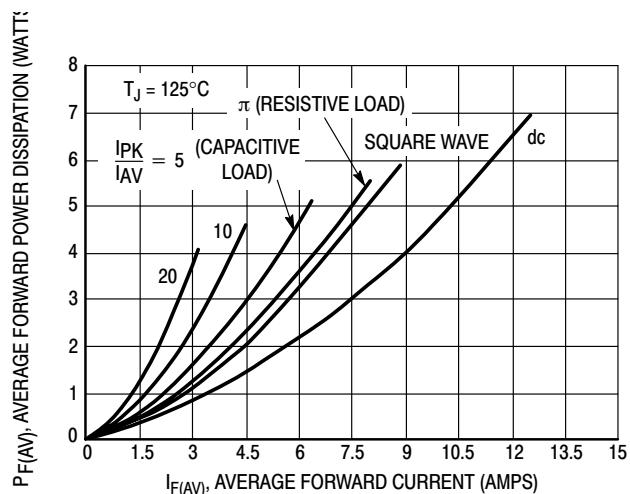
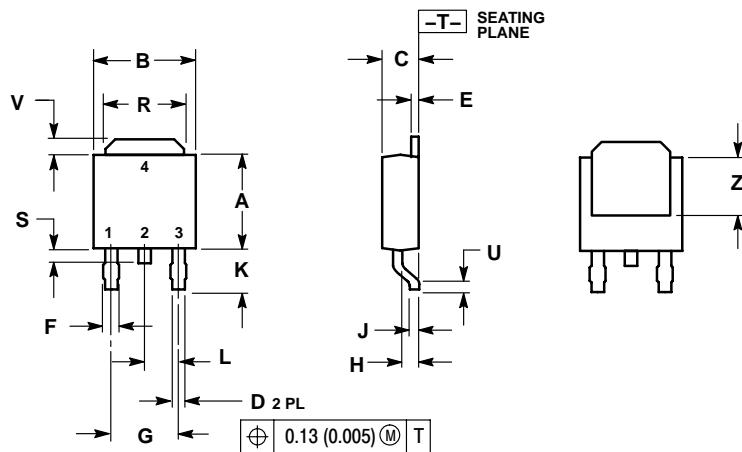


Figure 9. Forward Power Dissipation

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PACKAGE DIMENSIONS

DPAK
CASE 369C-01
ISSUE O

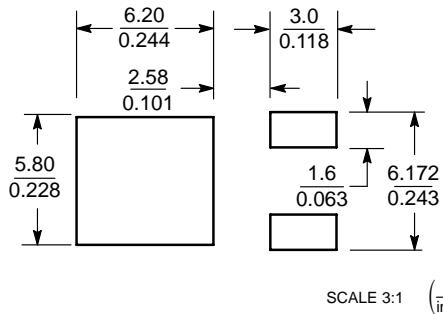


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180	BSC	4.58	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090	BSC	2.29	BSC
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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